Nanoelectronics in Japan and TIA
Part 4 of 7

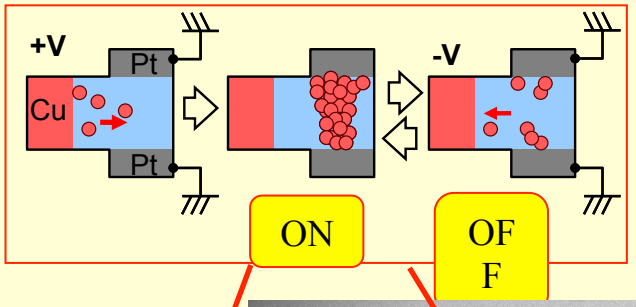
October 17 2013

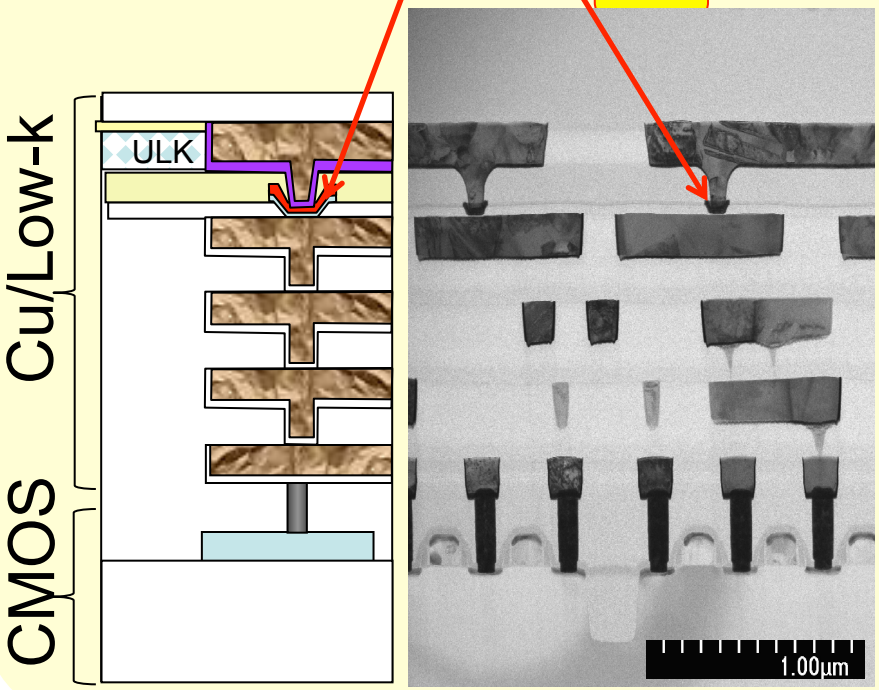
Shigeo Okaya AIST

New Materials and Devices for Low-Power Nanoelectronics

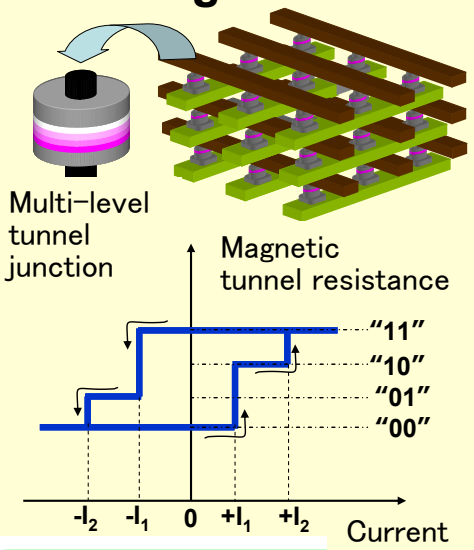
Reconfigurable logic LSI by Atom Switch

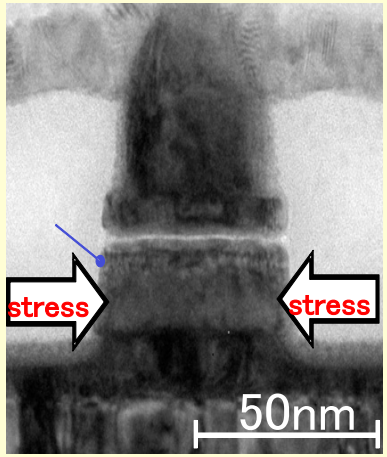
Functional Module (Atom SW)



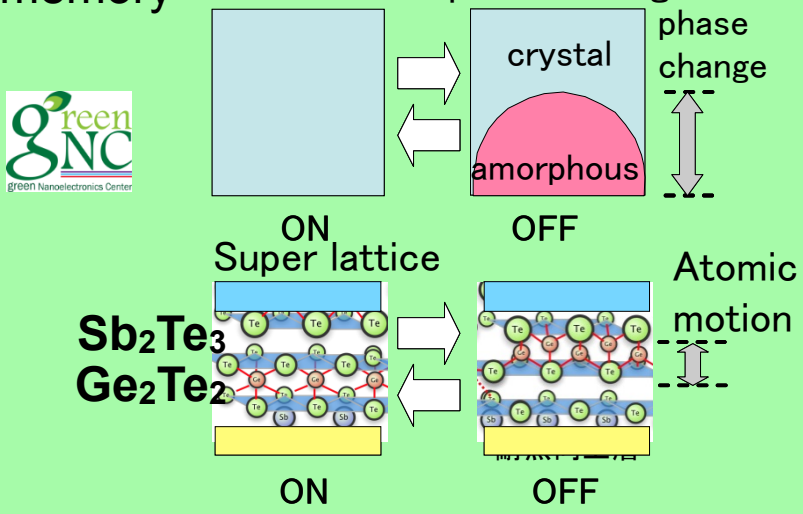


Multivalued magnetic tunnel junction memories



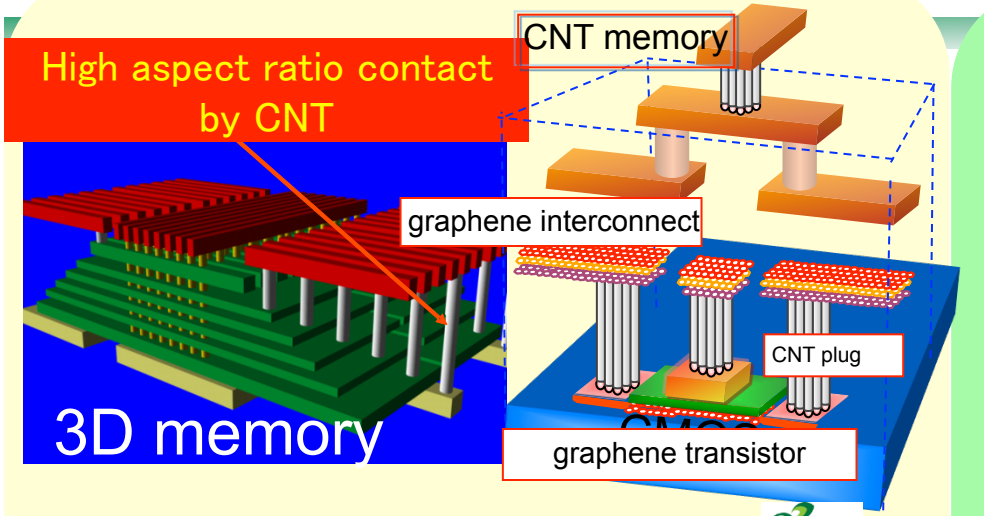


Chalcogen super-lattice phase-change memory

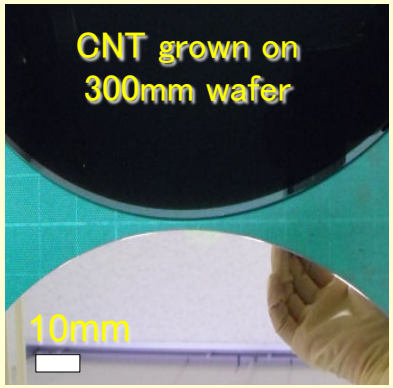


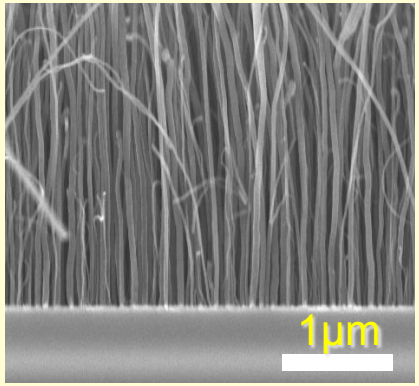
New Materials and Devices for Low-Power Nanoelectronics

TIA nano
Tsukuba Innovation Arena

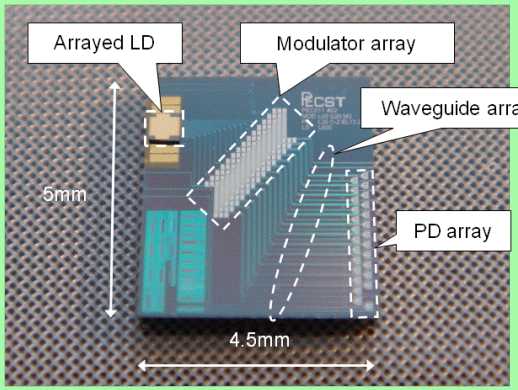


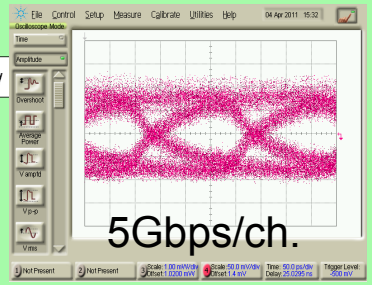
All carbon green nanoelectronics composed of CNTs and graphene



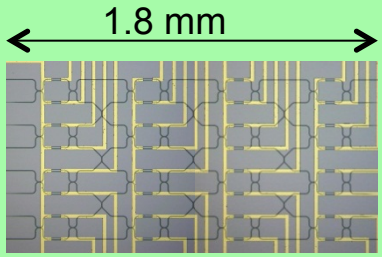


Si photonics
for low-power high-speed interconnect





3.5 Tbps/cm^2 transmission density was achieved.



4x4 Matrix switch
for dynamic optical path network